## **Correlation of Electron Tunneling and Plasmon Propagation in a Luttinger Liquid**

Sihan Zhao<sup>1†</sup>, Sheng Wang<sup>1,2†</sup>, Fanqi Wu<sup>3</sup>, Wu Shi<sup>1,2</sup>, Iqbal Bakti Utama<sup>1,2,4</sup>, Tairu Lyu<sup>1</sup>, Lili Jiang<sup>1</sup>, Yudan Su<sup>5</sup>, Siqi Wang<sup>6</sup>, Kenji Watanabe<sup>7</sup>, Takashi Taniguchi<sup>7</sup>, Alex Zettl<sup>1,2,8</sup>, Xiang Zhang<sup>2,5,9</sup>, Chongwu Zhou<sup>3,10</sup>\*, Feng Wang<sup>1,2,8</sup>\*

<sup>1</sup>Department of Physics, University of California at Berkeley, Berkeley, California 94720, USA.

<sup>2</sup>Materials Science Division, Lawrence Berkeley National Laboratory, Berkeley, California 94720, USA.

<sup>3</sup>Department of Chemical Engineering and Materials Science, University of Southern California, Los Angeles, California 90089, USA

<sup>4</sup>Department of Materials Science and Engineering, University of California at Berkeley, Berkeley, California 94720, USA.

<sup>5</sup>Department of Physics, State Key Laboratory of Surface Physics and Key Laboratory of Micro- and Nano-Photonic Structure (MOE), Fudan University, Shanghai 200433, China

<sup>6</sup>NSF Nanoscale Science and Engineering Center (NSEC), University of California at Berkeley, Berkeley, California 94720, USA

<sup>7</sup>National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-0044, Japan.

<sup>8</sup>Kavli Energy NanoSciences Institute at the University of California, Berkeley and the Lawrence Berkeley National Laboratory, Berkeley, California 94720, USA.

<sup>9</sup>Department of Physics, King Abdulaziz University, Jeddah 21589, Saudi Arabia.

<sup>10</sup>Department of Electrical Engineering, University of Southern California, Los Angeles, California 90089, USA

<sup>†</sup>These authors contributed equally to this work.

\*To whom correspondence should be addressed.

Email: <u>fengwang76@berkeley.edu</u> & <u>chongwuz@usc.edu</u>

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SM1. AFM image showing a representative SWNT cross junction device. Metal contacts are Pd/Au (10 nm/90 nm). The scale bar is 300 nm.



SM2. Transport data on individual metallic and semiconducting SWNTs characterized by near-field optical nanoscopy. (a) Transport data of an individual metallic SWNT (tube A in Fig. 2(c) in the main text) with weak dependence on backgate voltage (on/off < 5). (b) Transport data of an individual semiconducting SWNT (tube B in Fig. 2(c) in the main text) with strong dependence on backgate voltage (on/off > 1000). Measurements in (a) and (b) are carried out at room temperature in vacuum.

**SM2**.



SM3. A SWNT cross junction with a metallic SWNT crossing a semiconducting SWNT characterized by near-filed optical nanoscopy. (a) Near-field optical nanoscopy image of a SWNT cross junction comprised of a metallic SWNT (tube A with pronounced Luttinger liquid plasmons) and a semiconducting SWNT (tube B with no plasmon oscillations). (b) The corresponding AFM topography image of the same SWNT cross junction. Note that tube A forms a bundle with another tube on the right-hand side of this image. The scale bars in (a) and (b) are 200 nm.

SM3.



SM4. Power-law scaling with electrical bias in individual metallic SWNTs. (a) dI/dV results for the constituent metallic SWNT (tube 1-3 in Fig. 3(a)) at 15 K with the same backgate voltage as that used in Fig. 3(b). The power index from our best fitting is  $\alpha \sim 0.11$ , which corresponds to  $g \sim 0.70$  by using Eq. (2) in the main text. (b) dI/dV results for another isolated metallic SWNT measured at 20 K. The power index from our best fitting is  $\alpha \sim 0.23$ , which corresponds to  $g \sim 0.52$  by using Eq. (2) in the main text. The power scaling indexes vary significantly in different single SWNTs.



SM5. Correlation of electron tunneling and plasmon propagation in a Luttinger liquid in device #2. (a) Near-field optical nanoscopy characterization on a metallic SWNT cross junction. Luttinger parameters are determined to be  $g \sim 0.27$  (tube 1-3) and  $g \sim 0.29$  (tube 2-4) for each of two nanotubes from the measured Luttinger liquid plamons. Metal contacts are denoted by numbers. (b) Differential conductance (dIx/dVx) measurement of the electron tunneling probability across the Luttinger liquid junction as a function of voltage drop across the junction (Vx) at 20 K. Measurements are carried out in a four probe configuration where the electrical current is forced to flow through contacts 3 and 4 and voltage drop is measured through contacts 1 and 2. A power function fitting (blue line) yields  $g \sim 0.26$ . (c) The corresponding temperature-dependent electron tunneling data (zero Vx), which yields  $g \sim 0.30$ . (d) Scaled conductance (dIx/dVx) / T<sup> $\alpha$ </sup> as a function of eV / k<sub>B</sub>T at different temperatures, where  $\alpha$  is the power component with bias scaling at each temperature. All data collapse onto a single curve reasonably well, which provides an independent verification of Luttinger liquid behavior.